N-Channel 150-V (D-S) MOSFET

Key Features:

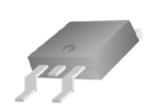
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

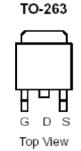
Typical Applications:

- · LED Inverter Circuits
- Inrush Limiter and Hot Swap Circuits
- 48V-Input DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
150	10 @ V _{GS} = 10V	90 ^a		
130	12 @ $V_{GS} = 6.5V$	90		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter		Symbol	Limit	Units			
rain-Source Voltage			150	V			
Gate-Source Voltage		V_{GS}	±20	V			
Continuous Drain Current a	T _C =25°C	I _D	90	А			
Pulsed Drain Current ^b		I _{DM}	360	A			
Continuous Source Current (Diode Conduction) a	T _C =25°C	I _S	90	Α			
Power Dissipation ^a	T _C =25°C	P_D	300	W			
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 175	°C			

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient °	$R_{\theta JA}$	62.5	°C/W			
Maximum Junction-to-Case	$R_{\theta JC}$	0.5	C/VV			

Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

Electrical Characteristics

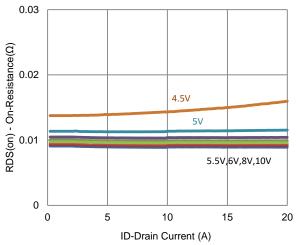
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	2			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	110			Α	
Drain Course On Besistance a	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			10	mO.	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 6.5 \text{ V}, I_{D} = 16 \text{ A}$			12	mΩ	
Forward Transconductance a	g_{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		60		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 45 \text{ A}, V_{GS} = 0 \text{ V}$		0.88		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 75 \text{ V}, V_{GS} = 6.5 \text{ V},$		55		nC	
Gate-Source Charge	Q_gs	$I_{D} = 20 \text{ A}$		20			
Gate-Drain Charge	Q_gd	1 _D = 20 / (20			
Turn-On Delay Time	$t_{d(on)}$	V 75 V B = 3 9 O		44			
Rise Time	t _r	$V_{DS} = 75 \text{ V}, R_{L} = 3.8 \Omega,$ $I_{D} = 20 \text{ A},$		56		ns	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		92			
Fall Time	t _f	VGEN = 10 V, NGEN 0 12		72			
Input Capacitance	C _{iss}			4329			
Output Capacitance	C _{oss}	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		462		pF	
Reverse Transfer Capacitance	C_{rss}			85			

Notes

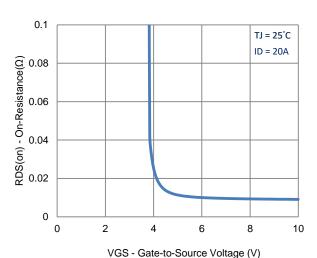
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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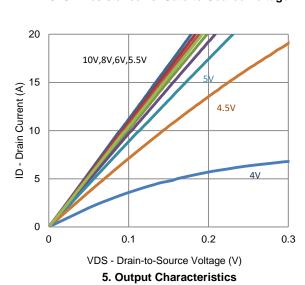
Typical Electrical Characteristics

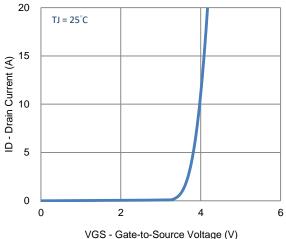


1. On-Resistance vs. Drain Current



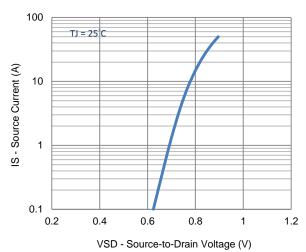
3. On-Resistance vs. Gate-to-Source Voltage



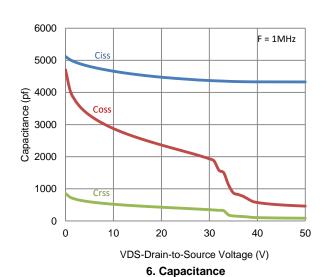


vGS - Gale-lo-Source vollage (v)

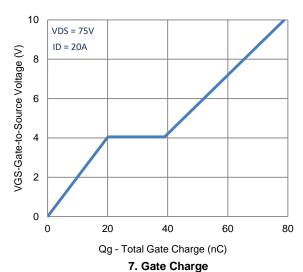
2. Transfer Characteristics

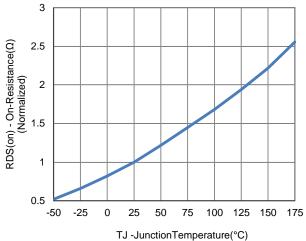


4. Drain-to-Source Forward Voltage



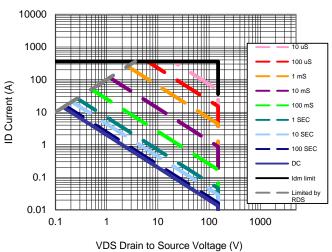
Typical Electrical Characteristics

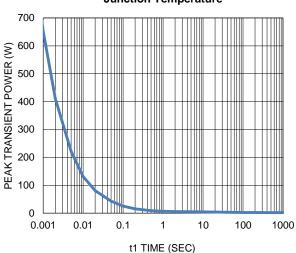




7. Oate Charge

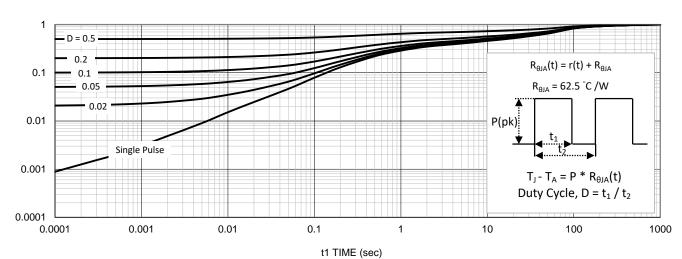
8. Normalized On-Resistance Vs Junction Temperature





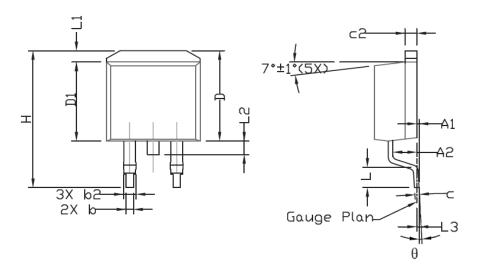
9. Safe Operating Area

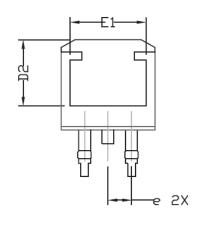
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information





CVAADEI	DIMENS:	IONAL F	REQMTS	INCH	ES REQMTS		
SYMBOL	MIN	NDM	MAX	MIN	NDM	MAX	
Α	4,30	4.57	4,72	0.169	0.180	0.186	
A1	0		0,25	0		0.010	
A2	2,47	2,57	2,67	0.097	0.101	0.105	
b	0.69	0,813	0.94	0.027	0.032	0.037	
b2	1,17	1,27	1,45	0.046	0.050	0.057	
C	0.48	0,50	0.60	0.019	0.020	0.024	
c2	1.17	1.27	1,37	0.046	0.050	0,054	
D	9,80	10.05	10,30	0.386	0,396	0.406	
D1	8,64	8.78	9,65	0,340	0,346	0.380	
D2	7.12	7.37	7,62	0.280	0,290	0.300	
E	9,70	10.15	10.54	0.382	0,400	0.415	
E1	8,00	8.20	8,40	0.315	0,323	0,331	
е	2,54 BSC			0.	100 BSC	,	
H	14,99	15,24	15,49	0.590	0.600	0.610	
L	1,78	2,29	2.79	0.070	0.090	0.110	
L1	1.02	1.27	1.52	0.040	0.050	0,060	
L2			1.75			0.069	
L3		0,254			0.010		
θ	0°		8•	0°		8°	